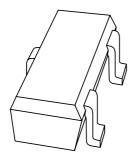
DISCRETE SEMICONDUCTORS

DATA SHEET



2PD602ANPN general purpose transistor

Product data sheet Supersedes data of 1997 Jun 20 1999 Apr 23



NPN general purpose transistor

2PD602A

FEATURES

• High current (max. 500 mA)

• Low voltage (max. 50 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

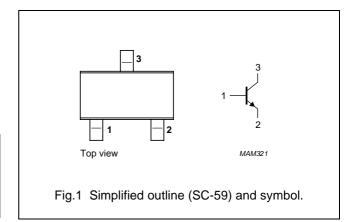
NPN transistor in an SC-59 plastic package. PNP complement: 2PB710A.

MARKING

TYPE NUMBER	MARKING CODE
2PD602AQ	XQ
2PD602AR	XR
2PD602AS	XS

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	1	Α
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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NPN general purpose transistor

2PD602A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 60 V	_	10	nA
		I _E = 0; V _{CB} = 60 V; T _j = 150 °C	-	5	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 4 V	_	10	nA
h _{FE}	DC current gain	$I_C = 150 \text{ mA}; V_{CE} = 10 \text{ V}; \text{ note 1}$			
	2PD602AQ		85	170	
	2PD602AR		120	240	
	2PD602AS		170	340	
	DC current gain	I _C = 500 mA; V _{CE} = 10 V; note 1	40	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 300 \text{ mA}$; $I_B = 30 \text{ mA}$; note 1	_	600	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	15	pF
f _T	transition frequency	I _C = 50 mA; V _{CE} = 10 V;			
	2PD602AQ	f = 100 MHz; note 1	140	_	MHz
	2PD602AR		160	_	MHz
	2PD602AS		180	_	MHz

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

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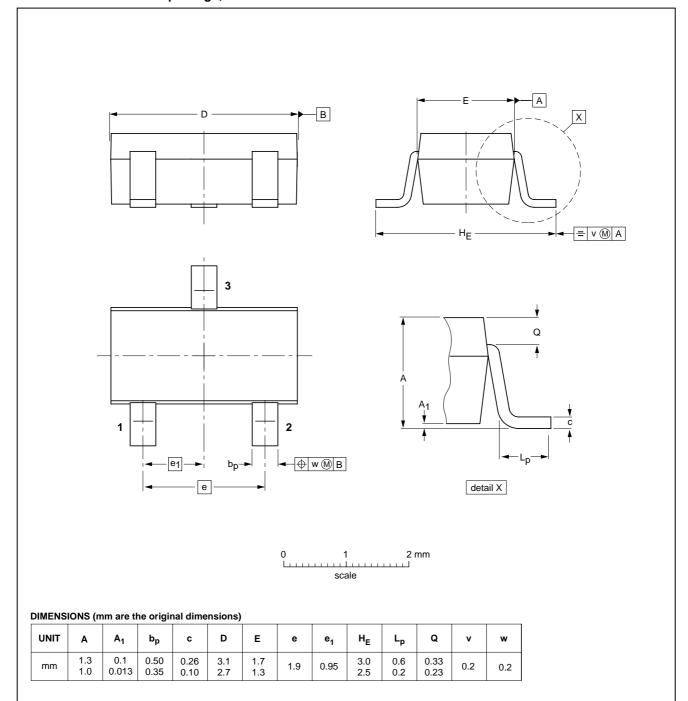
NPN general purpose transistor

2PD602A

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT346



REFERENCES

EIAJ

SC-59

JEDEC

TO-236

EUROPEAN

PROJECTION

ISSUE DATE

98-07-17

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IEC

OUTLINE

VERSION

SOT346

NPN general purpose transistor

2PD602A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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